Gate errors in solid state quantum com putation

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We review our work on the interplay between non-resonant gates and solid state environment in various solid state quantum computer architectures and the resulting gate errors. Particular, we show that adiabatic condition can be satis ed in small quantum dots, while higher energy excited states can play important role in the evolution of a Cooper-pair-box based quantum computer model. We also show that complicated bandstructure such as that of Si can pose a severe gate control problem.

I. IN TRODUCTION

It has been pointed out for a long time that quantum m echanics m ay provide great advantages over classical physics in physical computation [1,2]. The recent rapid grow th of research on quantum computation [3] started after Shor's factorization algorithm [4] and quantum error correction codes [5,6] were developed. For a quantum system to be used as a quantum computer (QC), it has to satisfy som e stringent conditions [7]. In short, it should possess a scalable Hilbert space; the state of such a system should be easily initialized; the system should have a long deocherence time; there should a set of universal unitary gates applicable to the system; and last but not least, every single quantum bit (qubit) of the system should be faithfully measured. Here we would like to review our work on the quantum gates and their operations in various solid state quantum com puter architectures.

Many two-level systems have been proposed as candidates for qubits in a solid state quantum computer. Typical examples include electron spins, nuclear spins, electron charge states, C ooper pair charge states, superconducting ux states, and m any m ore [8{14]. O ne m ajor motivation for these solid state devices is their potential in scalability. However, solid state structures also present com plex environm ents and fast decoherence rates [15]. Furtherm ore, in most solid state QC schemes, nonresonant gate operations [8,11,13,16] are crucial or im portant components. It is thus necessary to understand how the environm ental elements a ect the QC coherent evolution, and clarify the e ects of imperfections in nonresonant gate operations. In the follow ing, we will review som e of the results we have obtained for three di erent quantum computer architectures: the spin-based quantum dot QC, the Cooper-pair-box-based QC, and the donor-nuclear-spin-based SiQC.

II.NON-ADIABATIC OPERATIONS IN A DOUBLE QUANTUM DOT

Let us rst discuss our work on the spin-based quantum dot quantum computer (Q D Q C) in G aA s [8,9]. Here two-qubit operation is based on the nearest neighbor exchange coupling, which produce the exchange splitting between the ground singlet and triplet states. For sm all quantum dots, with large single particle excitation energy E_s and large on-site C oulom b repulsion energy E_c and at $m \inf E_s; E_c g$), the low energy low tem peratures ($k_B T$ dynamics is dominated by the electron spins. In other words, one can focus on the spin part of the two-electron Hilbert space that involves only the ground singlet and triplet states and cut o the rest of the Hilbert space. For example, at T 100 m K and with m in $fE_s; E_c q$ 1 m eV, the therm aloccupation of the higher energy orbital states is less than 10 50 , which can be safely neglected. Thus one can quite faithfully prepare a single electron in a single dot in its ground orbital state and/or two electrons in a double dot in the ground singlet/triplet state manifold. For a double dot, after the state is initialized, as long as the applied quantum gates satisfy adiabatic condition, the system would remain in the ground state m anifold, so that H eisenberg exchange H am iltonian would describe the dynam ics of the double quantum dot exactly. How ever, the size of a gated quantum dot is lim ited from below by gate and device dimensions, while the gate operating time is limited from above by the electron spin decoherence time. Thus it is necessary to quantitatively assess the adiabatic condition for two-qubit operations in a double dot of realistic dimensions, so as to determ ine whether exchange gates can be su ciently fast to guarantee a large gate-tim e/decoherence-tim e ratio while slow enough to produce correctably sm all non-adiabatic errors.

We have performed a quantitative evaluation of the adiabatic condition in a double quantum dot [17] using the results of ourm olecular orbital calculation of the double energy spectra [9]. Speci cally, we prepare a twoelectron state in the ground singlet state with a high barrier between the double dot. As the system evolves, the barrier height between the two dots is rst low ered, then raised back to the original value. If H eisenberg exchange H am iltonian is exact for this system, its state should remain in the ground singlet state. A ny loss from this state would then constitute a leakage from the QC H ilbert space and a gate error.

Our calculation is essentially an integration of the time-dependent Schrodinger equation for the twoelectron double quantum dot:

$$\frac{@_{O_{k}}(t)}{@t} = \frac{X^{k}}{\sum_{i \in k} \frac{C_{i}(t)}{E_{k}(t) - E_{i}(t)}} hk_{j}\frac{@H_{i}(t)}{@t} jii$$

$$exp_{i}\frac{1}{ih} \sum_{i}^{Z_{t}} (E_{i}(\cdot) - E_{k}(\cdot))d : (1)$$

Here c_k (t) are the coe cients as we expand the twoelectron, state on the instantaneous eigenstates jki: $_{k}$ Q_k (t)u_k (t) and H (t)u_k (t) = E $_{k}$ (t)u_k (t), where (t) = H (t) is the time-dependent system Hamiltonian. The explicit time-dependence of H is in the inter-dot barrier height. Since initially the system is entirely in the ground singlet state, q_k (t = 0) = k_0 for all k. The energy spectra we use are for a double dot with Gaussian con nem ents of 30 nm radii and 40 nm inter-dot distance [9]. The energy barrier height $V_{\rm b}$ ranges between 14 m eV and 35 m eV, corresponding to exchange splitting of 280 eV to 3.3 eV. By varying the barrier variation time, we can quantitatively evaluate the change in the ground singlet state population, thus obtaining a lower lim it to the gate operating time using the criterion of quantum error correction code threshold.

The result of our calculation is plotted in Fig. 1 [17]. The leakage (y-axis) is de ned as 1 ją∱ which is zero before the gate is applied, and should be zero if the gate is perfectly adiabatic. A side from several interesting features [17], Fig. 1 dem onstrates that for gating tim e longer than 30 40 ps, leakage in our double dot system should be su ciently sm all ($< 10^{6}$) so that the currently available quantum error correction schemes would be e ective. On the other hand, an exchange splitting of 0.1 m eV corresponds to about 20 ps gating time for a swap gate [8] (with rectangular pulse) at the shortest. Therefore, adiabatic condition does not place an extra burden on the operation of the two-qubit gates such as a swap there is in general no need to signi cantly increase the gating tim e in order to accom m odate the adiabatic requirem ent.

N otice that the current calculation is done for a pair of quite sm allquantum dots. Largerdots would have m eant sm aller excitation energies and a threshold gating tim e that is longer in order to satisfy the adiabatic condition.

III.NON-SUDDEN OPERATIONS IN A COOPER PAIR BOX

A nother example we have considered is the Cooperpair box quantum computer (CPBQC) [17]. The Ham iltonian of a Cooperpair box (CPB) can be written on the basis of charge number states of the box:

$$H = 4E_{C} (\hat{n} n_{g})^{2} E_{J} \cos^{\hat{n}}$$

$$= 4E_{C} (n n_{g})^{2} \hat{j} \hat{l} \hat{l} \hat{n} \hat{j}$$

$$\frac{E_{J}}{2} (\hat{j} \hat{l} \hat{l} \hat{n} + 1 \hat{j} + \hat{j} \hat{n} + 1 \hat{l} \hat{l} \hat{n} \hat{j}); \qquad (2)$$

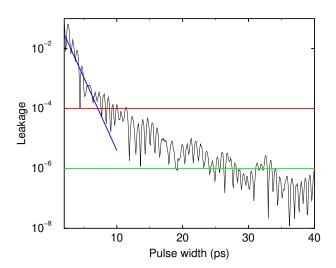


FIG.1. Leakage as a function of the pulse width 2 of the exchange gate. The two-electron state is initially in the ground singlet state. The two horizontal lines represents the commonly used thresholds for quantum error correction. The tted line at the small pulse-width indicates the initial rapid decrease in the error rate (leakage) as the pulse becom eswider (or the gate operation becom es slower).

where E_c is the charging energy of a CPB, E_J is the Josephson coupling between the CPB and an external superconducting lead, n_g represents the applied voltage on the CPB in term s of an electrice charge number, and n refers to the number of extra Cooper pairs in the box. D ue to the periodic nature of the Josephson coupling, the eigenstates of a CPB form energy bands. The two states j"i and j#i for a CPB qubit correspond to the two lowest energy levels at $n_g = 1=2$, where the eigenstates are approximately j#i = (jDi + jLi) = $\frac{P}{2}$ and j"i = (jDi + jLi) = $\frac{P}{2}$ with a splitting of about E_J .

Sim ilar to the case of Q D Q C discussed above, higher excited states play an important role in the dynam ics of a CPBQC when it is subjected to non-resonant operations [18]. The particular operation we considered is the sudden pulse gate to shift n_{α} , thus bringing a system from a pure ground state ($\text{piat}, \text{e.g.} n_{g} = 1=4$) to a coherent superpositioned state ((j''i+j#i)=2 at $n_{g} = 1=2$). Such a simple description of the pulse gate is only valid when $E_J = E_C$! 0. Since E_J determ ines the gate speed of a CPBQC, such a condition is not practical for a realistic QC.Furtherm ore, in real experim ents, the pulse gate alwayshas nite rise/falltimes (non-sudden). In Ref. [16], the pulse rise time is in the range of 30 to 40 ps. Such gradual rise and fall of the pulse gate inevitably lead to m ore errors, which have been considered in the context of two-level system s [16,19,20]. W hat we have done is to calculate the delity of the pulse gate taking into account the nite rise/falltime, the higher excited states, and the com plete com position of all the eigenstates [17].

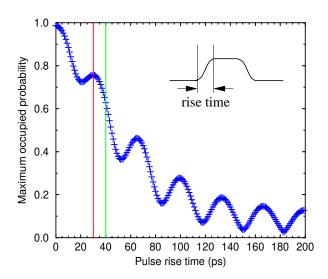


FIG.2. State delity as a function of the nite rise/fall time of a pulse gate in a single Cooper pair box. The – delity here is de ned as the maximum probability (which in – plies particular choices of pulse duration $_{\rm p}$ as this probability varies periodically with $_{\rm p}$) of the CPB in the rst excited state after the application of a pulse gate with the state starting from the ground state (represented by ng goes from 0.255 to 0.5, then back to 0.255 after a period of time $_{\rm p}$). The CPB is treated as a multi-level system (on the basis of j 10i; ; j0i; j1i; ; j10i). The lineshape of the rise/fall of the pulse is a sinusoidal function of time. The system param eters are chosen as the values used in Ref. [16]. The two vertical lines give the range of rise/fall time from the sam e source.

In Fig. 2 we plot the state delity as a function of rise time. Here the state delity is de ned as the maximum probability for the CPB to be in the rst excited state after the pulse gate when n_g returns to 0.255. Figure 2 shows that the delity of the pulse gate decreases oscillatorily instead of monotonically as the pulse rise time increases. The oscillations (with periods around 30 ps) in the curves represent the coherent evolution of the CPB during the rise/fall of the pulse voltage. For pulses used in Ref. [16] with rise/falltime in the range of 30 to 40 ps, the delity is only 60 to 70%, apparently not su cient for manipulations required by quantum computation. Further calculations also dem onstrate that including higher excited states is in portant in correctly evaluating the delity dependence on the rise time of the non-resonant sudden pulse gate [17].

IV . IM PLICATIONS OF SIBANDSTRUCTURE

The previous two examples demonstrate the interplay of non-resonant gate operations and states from the full Hilbert space, and the resulting leakage from the com putational space. Solid state environment can a ect the

operation of a quantum computer in other subtle ways. For example, modern technology can produce extremely pure silicon crystals which have the intrinsic property of very small spin-orbit coupling. Thus electron and nuclear spins in Si have a very \quiet" environment the spin relaxation times are extremely long in Si [21,22]. It is therefore natural to use Sias a host material for spinbased quantum com puter architectures [11]. How ever, Si is an indirect gap sem iconductor. There are actually six equivalent m in in a in its conduction band that are away from the center of the Fist Brillouin zone and close to the zone boundary. The implication of this complexity is that con ned electron states (whether the con nem ent is provided by a donor or a gate-produced electrostatic potential in the form of a quantum dot) in general have contributing components from all the valleys, which can then lead to atom ic scale spatial oscillations of electronic properties such as electron density and two-electron exchange coupling.

We have performed a Heitler-London calculation for the two-electron exchange splitting for two phosphorus donors in Si [23]. The SiP system is being studied as a candidate of nuclear spin based quantum computers [11,24]. Donorelectron exchange is a crucial intermediary in the elective nuclear spin exchange interaction that is the basis of the two-qubit operations in such a quantum

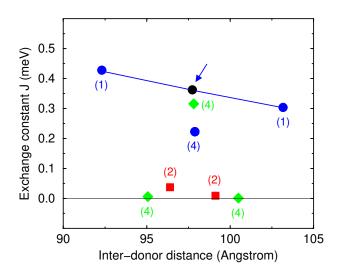


FIG.3. Variations in the exchange coupling between two phosphorus donors in Si. The arrow points at the circle that represents the value of electron exchange at the reference conguration with the two donors exactly along the [100] direction and separated by 18 lattice constants. The circles connected by a line refer to pairs along the [100] direction, displaced by one lattice constant with respect to the reference position. The rest of the sym bols represent displacements of one member of the donor pair into one of its rst (squares), second (diamonds), or third (circles) nearest neighbor positions. The numbers in the parenthesis next to the sym bols are their degeneracies, respectively.

com puter architecture. Our calculation indeed shows a fast-varying exchange, as is dem onstrated in Fig. 3, which shows that a m ovem ent of one m em ber of the donor pair into its nearest or second nearest neighbor sites can com – pletely suppress the exchange coupling between the two donor electrons.

In the original proposal of Siquantum computer [11], electron exchange is tuned by applied gate voltages, which would shift the electron wavefunctions. Thus the two-qubit gates here are exposed to the atom ic-scale oscillations. The direct implication of the oscillatory exchange is that the gate voltages corresponding to the peak exchange coupling have to be well-controlled, optim ally close to a local maximum where the exchange is least sensitive to the gate voltage. Since the oscillatory exchange period is close to lattice spacing, the positioning of the donor electrons by the surface gates must be controlled at least to that precision.

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